

Patent Abstracts of Japan

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PUBLICATION NUMBER : 11111979  
PUBLICATION DATE : 23-04-99

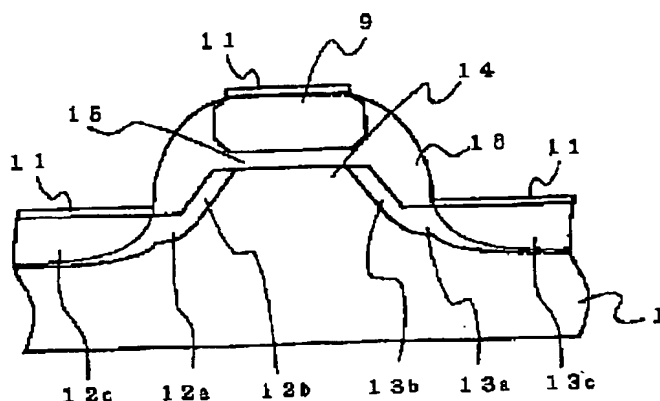
APPLICATION DATE : 30-09-97  
APPLICATION NUMBER : 09267191

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INT.CL. : H01L 29/78 H01L 21/265 H01L 21/28  
H01L 29/41 H01L 21/336

TITLE : SEMICONDUCTOR DEVICE AND ITS  
MANUFACTURE



ABSTRACT : PROBLEM TO BE SOLVED: To obtain a semiconductor device which can be driven at a high speed, while the occurrence of a short channel effect is suppressed even if the device is made finer.

SOLUTION: Since a semiconductor device has a structure such that a source region 12 and a drain region 13 are bent toward a gate electrode 9, with the regions 12 and 13 being partially protruded, the regions of the source and drain regions 12 and 13 facing the gate electrode 9 become smaller, and the parasitic capacitances between the gate electrode 9 and the source and the drain regions 12 and 13 can be reduced. In addition, since the impurity concentrations in the protruded sections are lower, no wide space-charge region is formed around the protruded sections. Therefore, the occurrence of a short-channel effect can be prevented.

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